

**/ Descriptions**

Silicon PNP transistor in a TO-92LM Plastic Package.

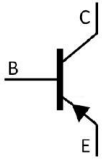
**/ Features**

Complementary pair with 2SD667(A).

**/ Applications**

Low frequency power amplifier.

**/ Equivalent Circuit**



**/ Pinning**



PIN1 Base      PIN 2 Collector      PIN 3 Emitter

**/  $h_{FE}$  Classifications & Marking**

| $h_{FE}$ Classifications<br>Symbol | B      | C       | D       |
|------------------------------------|--------|---------|---------|
| $h_{FE}$ Range                     | 60 120 | 100 200 | 160 320 |

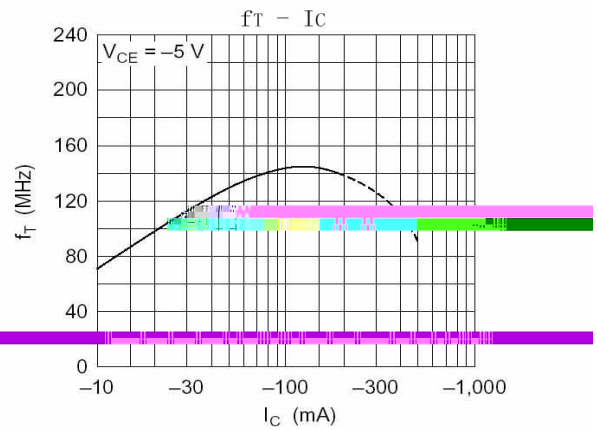
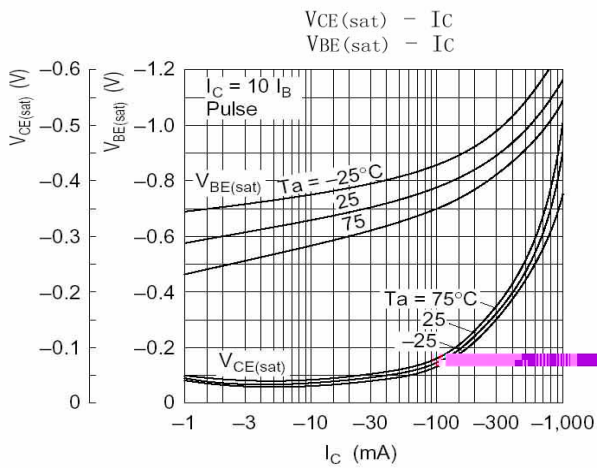
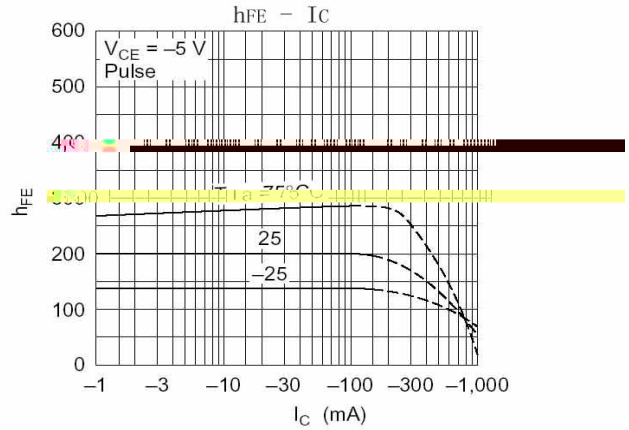
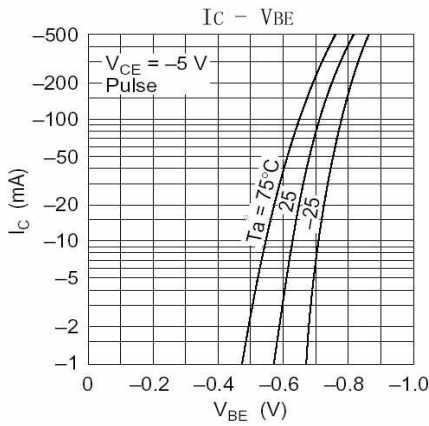
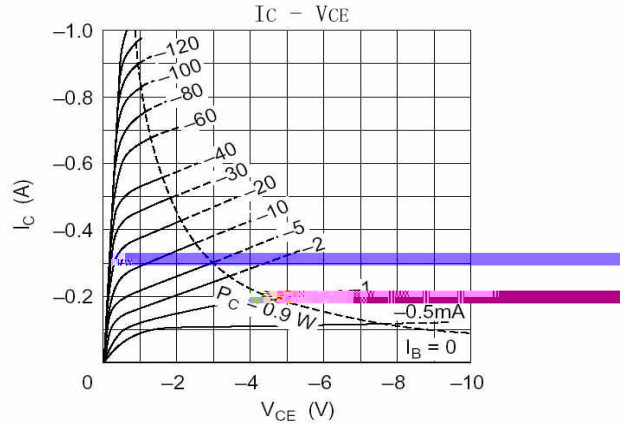
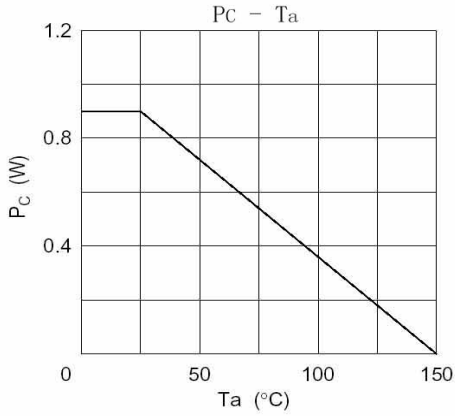
## / Absolute Maximum Ratings(Ta=25 )

| Parameter                    | Symbol    | Rating  | Unit |
|------------------------------|-----------|---------|------|
| Collector to Base Voltage    | $V_{CBO}$ | -120    | V    |
| Collector to Emitter Voltage | $V_{CEO}$ | 2SB647  | -80  |
|                              |           | 2SB647A | -100 |
| Emitter to Base Voltage      | $V_{EBO}$ | -5.0    | V    |
| Collector Current (DC)       | $I_C$     | -1.0    | A    |
| Collector Current(Pulse)     | $I_{CP}$  | -2.0    | A    |
| Collector Power Dissipation  | $P_C$     | 900     | mW   |
| Junction Temperature         | $T_j$     | 150     |      |
| Storage Temperature Range    | $T_{stg}$ | -55 150 |      |

## / Electrical Characteristics(Ta=25 )

| Parameter                               | Symbol        | Test Conditions                     | Min  | Typ | Max  | Unit    |
|---|---------------|-------------------------------------|------|-----|------|---------|
| Collector to Base Breakdown Voltage     | $V_{CBO}$     | $I_C=-10\mu A$ $I_E=0$              | -120 |     |      | V       |
| Collector to Emitter Breakdown Voltage  | $V_{CEO}$     | $I_C=-1.0mA$ $R_{BE}=\infty$        | -80  |     |      | V       |
|   |               |                                     | -100 |     |      |         |
| Emitter to Base Breakdown Voltage       | $V_{EBO}$     | $I_E=-10\mu A$ $I_C=0$              | -5.0 |     |      | V       |
| Collector Cut-Off Current               | $I_{CBO}$     | $V_{CB}=-100V$ $I_E=0$              |      |     | -10  | $\mu A$ |
| DC Current Gain                         | $h_{FE(1)}$   | $V_{CE}=-5.0V$ $I_C=-150mA$         | 60   |     | 320  |         |
|   | $h_{FE(2)}$   | $V_{CE}=-5.0V$ $I_C=-500mA$         | 30   |     |      |         |
| Collector to Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C=-500mA$ $I_B=-50mA$            |      |     | -1.0 | V       |
| Base to Emitter Voltage                 | $V_{BE}$      | $V_{CE}=-5.0V$ $I_C=-150mA$         |      |     | -1.5 | V       |
| Transition Frequency                    | $f_T$         | $V_{CE}=-5.0V$ $I_C=-150mA$         |      | 140 |      | MHz     |
| Collector Output Capacitance            | $C_{ob}$      | $V_{CB}=-10V$ $I_E=0$<br>$f=1.0MHz$ |      | 12  |      | pF      |

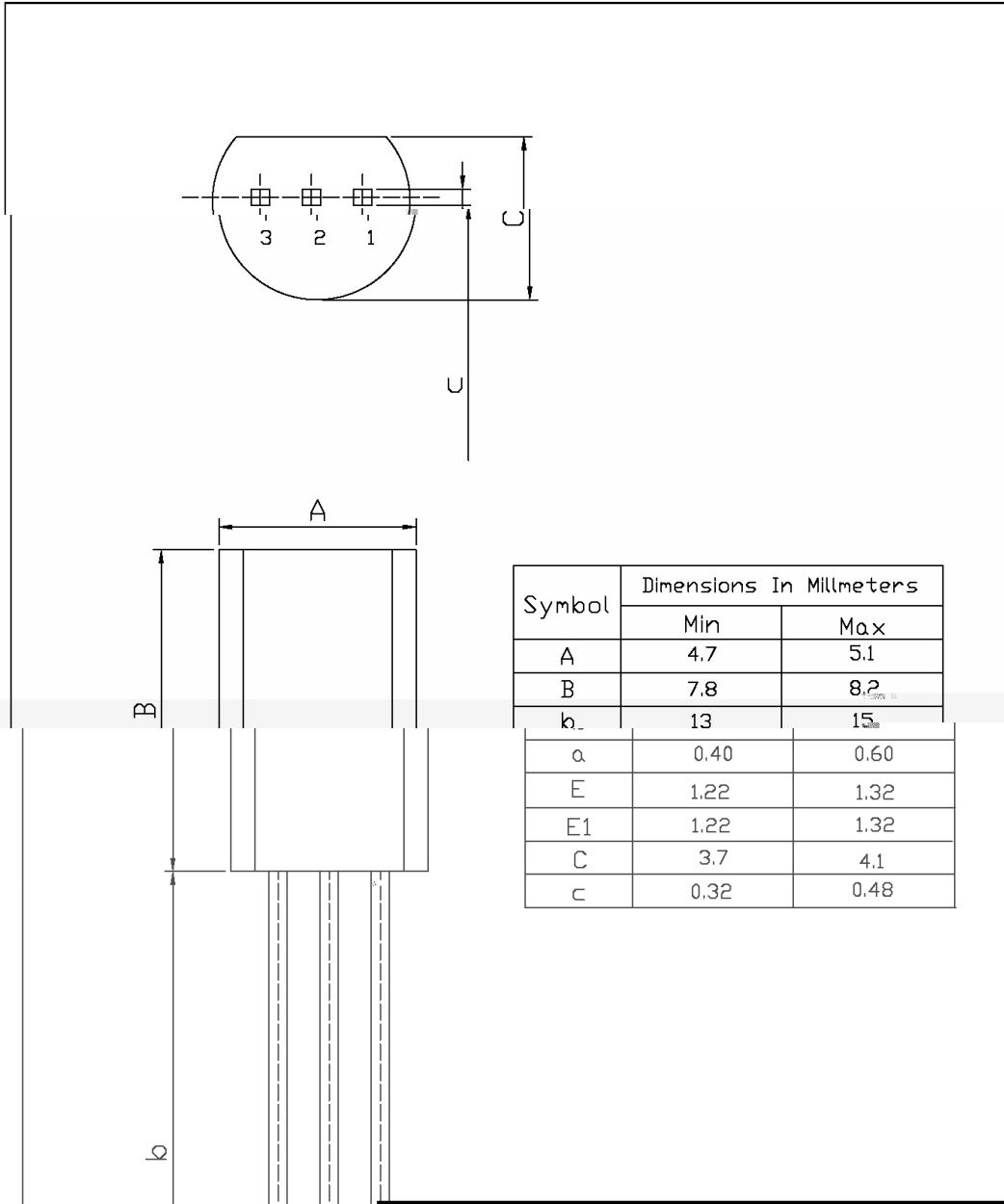
**/ Electrical Characteristic Curve**



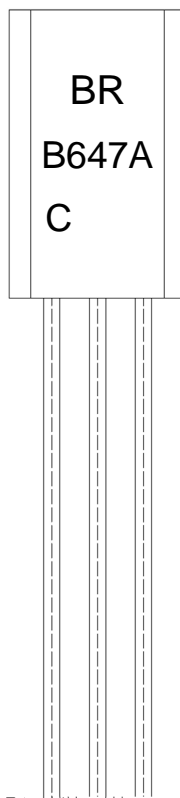
**/ Package Dimensions**

T0-92LM

Unit: mm



/ Marking Instructions



Note:

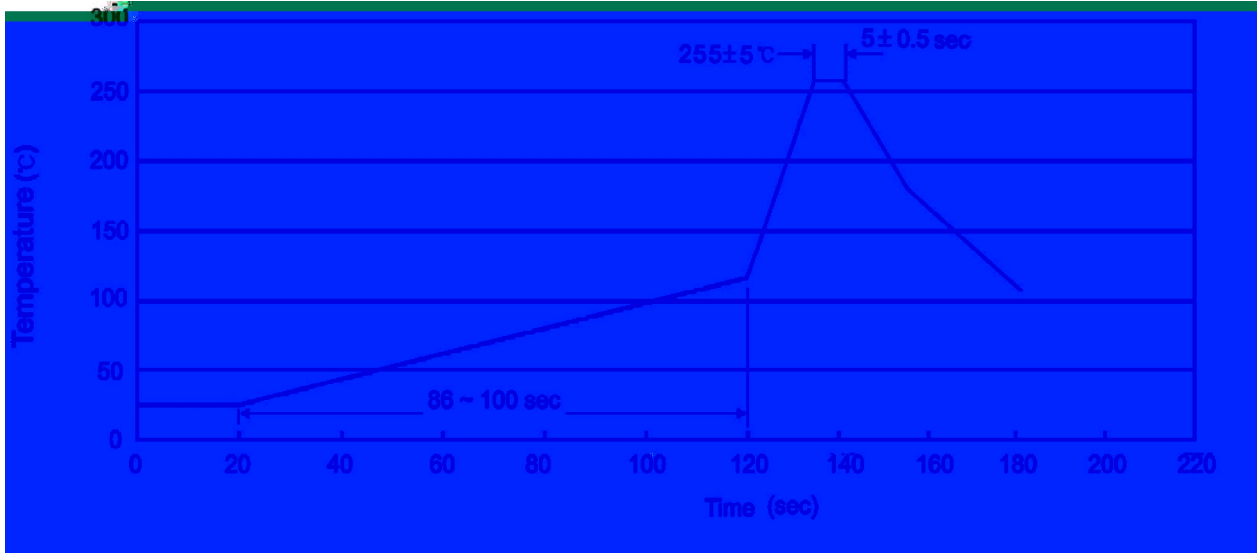
BR: Company Code.

B647A: Product Type.

C:  $h_{FE}$  Classifications Symbol

\*\*\*\*: Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



Note:

1            25   150            60   90sec;

1.Preheating:25~150 x 1'D